Tests of Silicon Strip Modules for the Upgrade of the ATLAS Detector at the LHC

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Outline

* ATLAS Detector at LHC & Upgrade: HL-LHC and PETAL2014

- Readout System Setup
- Readout Software & Test results
- * Database
- * Systematic Study of Readout System
- Summary & Conclusion & Outlook





HL-LHC & ATLAS Upgrade

Semiconductor Tracker (SCT)

HSIO Readout System

SCTDAQ Readout Software & Test Results

Database Systematic Study

The Large Hadron Collider (LHC)



HL-LHC & ATLAS Upgrade

Semiconductor Tracker (SCT)

SCTDAQ Readout Software & Test Results

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Systematic Study

The Current ATLAS Detector





Upgrade of LHC

HL-LHC (High Luminosity Large Hadron Collider)

- * Upgrade of LHC & ATLAS Detector
 - to reduce the statistical uncertainties for measurements
- * the expected luminosity after upgrade in 2020: $5 \times 10^{34} \text{ cm}^{-2} \text{s}^{-1}$
- * effects of higher luminosity for the detector: higher occupancy, higher radiation

*upgrade:

higher granularity, increased electronic channels, radiation hardness, new powering schemes





Plots of tracks Simulation of ATLAS detector



Semiconductor Tracker (SCT)

Database Systematic Study

Proposed Layout of the Inner Detector





Upgrade of Silicon Strip Detector



0.4 m



<----- Testing Module

HL-LHC & ATLAS Upgrade

SCTDAQ Readout Software & Test Results

Database Systematic Study

HSIO (High-Speed Input/Output) Readout System



Dummy Module



HL-LHC & ATLAS Upgrade	Semiconductor Tracker (SCT)	HSIO Readout System	SCTDAQ Readout Software & Test Results	Database	Systematic Study				
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- Binary readout architecture
- Charge injection (to simulate a particle passing through the detector)
- 2 Amplitude above the threshold : a hit "I", below the threshold : no hit "0"
- 3. Trigger is sent to readout the hits



readout chip -----> ATLAS Binary Chip- Next (ABCN 25)

Database Systematic Study

Structure of Redout System (Current)

 Offline-Detector Readout Devices : VME units (CLOAC, SLOG, MuSTARD) are replaced by HSIO for the upgrade









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Top level routine : in C++ & ROOT

* Lower level routine : in C



Threshold Scan - basic concept of readout

- SCTupDAQ is the threshold scan based examinations
- Scan through thresholds with a fixed value of injected charge



$$S(x) = \frac{1}{2}\operatorname{erfc}(x) = \frac{1}{2}(1 - \operatorname{erf}(x)) = \frac{1}{2} - \frac{1}{\sqrt{\pi}}\int e^{-x^2} \,\mathrm{d}x = \frac{1}{2} - \frac{1}{\sqrt{\pi}}\int G(x) \,\mathrm{d}x \qquad \qquad x = \frac{\operatorname{Vt}50 - \mu_s}{\sqrt{2}\sigma_s}$$





Result of Dummy Module M59 strun 661 @Zeuthen



SD 0.40 is used in the situation of large channel to channel variation

Result of Barrel_Hybrid stream 0 strun 393 @Birmingham





Threshold scan with different injected charge

Response Curve shows linear behavior for lower injected charge

Linear Fit	$g = rac{Vt50_2 - Vt50_1}{q_2 - q_2} = p_1$
Exponential Fit	$g = rac{p_0 e^{-rac{q}{p_1}}}{p_1 \left(1 + e^{-rac{q}{p_1}} ight)^2}$
Grillo Function Fit	$g = \frac{p_1}{\left(1 + \frac{p_1^2 q^2}{p_1^2}\right)^{\frac{3}{2}}}$
Polynomial Fit	$g = p_1 + 2p_2q$

- g, Gain (mV/fC)
- q, Injected Charge (fC)
- p_0 , Offset (mV)
- p_1 , Small Signal Gain
- p_2 , measurement of the non-linearity

Result of Dummy Module M59 strun 661 @Zeuthen SCTDAQ.trunk 1768

Chip 1 Response Curve

Entries



Charge(fC)



HL-LHC & ATLAS Upgrade	Semiconductor Tracker (SCT)	HSIO Readout System	SCTDA	Q Readout Softw	are & Test Results	Database	Systematic Study
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							Page.20

	Injected Charge (fC)									
3PT 1fC	0.52		1.00	_	1.48	-	_		—	-
3PT 2fC	-		-	-	1.52	2.00	2.48	-	-	-
RC	0.52	0.76	1.00	1.24	1.52	2.00	3.00	4.00	6.00	7.00

	m59 (ENC)	m60 (ENC)
3PointGain 1fC	365 ± 20	373 ± 21
3PointGain 2fC	367 ± 21	378 ± 22
Response Curve	371 ± 18	383 ± 18

Input Noise Values

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3PT (IfC) ~ 3PT (2fC) < RC
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Output Noise values are at the same level, it might be due to the lower gain for higher injected charge

HL-LHC & ATLAS Upgrade	Semiconductor Tracker (SCT)	HSIO Readout System	SCTDA	Q Readout Softw	are & Test Results	Database	Systematic Study
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- Gain Test result of all 1280 channels (10 chips)
- * Vt50 at injected charge of 2fC
- Input Noise
 The main index now commonly used in SCT community to determine the performance of the module or system





HL-LHC & ATLAS Upgrade	ATLAS Upgrade Semiconductor Tracker (SCT) HSIO Readout S		SCTDA	Q Readout Softw	vare & Test Results	Database	Systematic Study
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- To keep the homegeneity of performance across all channels, Threshold for each channel has to be tuned
- 8 target thresholds are acuqired to be trimmed (with 8 different trim steps and ranges),
- The channels are not able to be trimmed, they are masked



Result of Dummy Module strun 661 @Zeuthen SCTDAQ.trunk 1768



- 8+1 different trim and mask results the optimize one: * I. less masked channels
 - 2.smaller trim ranges
- Number of Masked Channels If the target threshold can not be trimmed by small trim step, there are more channels masked than the larger trim range



Result of Dummy Module strun 661 @Zeuthen SCTDAQ.Windows version

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- Measured without injecting charge
- * Send 2000 triggers to readout the signal
- Reduce the statistical error by sending more triggers



Result of Dummy Module strun 570 @Zeuthen Modified Version



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Database Systematic Study

System Stability - Electromagnetic Interference

* Example :

The bunch crossing clock signal during the test of single hybrid

Electromagnetic impose noise on the bunch crossing clock signal in extreme case, can crash the readout software



Database Systematic Study

Noise Hunting - Different Way to Power HSIO

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Powering the HSIO without large DC-DC converters (noisy)

Other group observe different behavior (under investigation)

	m59 (3PT 1fC)	m59 (3PT 2fC)	m60 (3PT 1fC)	m60 (3PT 2fC)
48 V	401 ± 21	449 ± 27	403 ± 29	453 ± 33
12 V	412 ± 25	464 ± 29	409 ± 29	464 ± 67

- ***** Upgrade of LHC & ATLAS Detector
- * DESY focus on module production and testing
- HSIO based readout system and the SCTupDAQ software set up (further debugging is still on going)
 ready for the future module production & testing
- * Test results of dummy module
 - Strobe Delay, Gain tests, Trim Range, Noise Occupancy
- * The Zeuthen Database
 - Modified the interface to local database
- Stability and Noise hunting of the readout system
 - The sources of system instability identified, noise hunting season has not yet ended

\ast the behaviour of In(O) should be linear as the theory predicted

$$\ln(O) \approx -\frac{1}{2} V_{\rm thr}^2 - \ln\left(\sqrt{2\pi} V_{\rm thr}\right)$$

Electromagnetic Interference

* The bunch crossing clock signal during the test of signal hybrid

 \ast The signal from electromagnetic interference superpositon the bunch crossing clock signal and make the readout terminated

Trim DAC Code (bit2 bit1 bit0)	Trim DAC range	Trim DAC step
000	0 mV - 14.88 mV	0.48 mV
001	0 mV – 22.32 mV	0.72 mV
010	0 mV – 29.76 mV	0.96 mV
011	0 mV - 37.20 mV	1.20 mV
100	0 mV - 44.64 mV	1.44 mV
101	0 mV - 59.52 mV	1.92 mV
110	0 mV - 74.40 mV	2.40 mV
111	0 mV - 89.28 mV	2.88 mV

